

Effects of unreacted Mg impurities on the transport properties of MgB_2

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 (Dated: March 22, 2022)

We synthesized polycrystalline MgB_2 from a stoichiometric mixture of Mg and the ^{11}B isotope under different conditions. All the samples showed bulk superconductivity with $T_c = 38 \sim 39$ K. The samples containing the least amount of unreacted Mg showed the highest T_c and the sharpest transition width (ΔT_c). A residual resistivity ratio (RRR) of ~ 5.8 , and a magnetoresistance (MR), at 40 K, of 12% were obtained for these samples. Moreover, there was no upturn of resistivity in a low temperature region at 10 Tesla. The samples containing appreciable amounts of unreacted Mg showed quite different behaviors; the values of ΔT_c , RRR, and MR were much larger. An upturn appeared in resistivity of the samples below about 50 K at 10 T and is thought to be due to the unreacted Mg.

PACS numbers: 74.25.Fy, 74.60.-w, 74.70.Ad, 74.72.-h

The recent discovery¹ of the binary metallic MgB_2 superconductor has attracted great scientific^{2,3,4,5,6,7,8} and industrial^{2,9} interest. Even though basic issues, such as the isotope effect³ and the determination⁴ of the carrier type, were addressed immediately, there still exist conflicting results. For example, several groups^{2,5,6,10,11,12,13,14,15} have measured the transport properties of their polycrystalline MgB_2 and have reported different values for the residual resistivity ratio (RRR), magnetoresistance (MR), residual resistivity. The widely accepted opinion was that good bulk samples of MgB_2 (called ‘*highRRR-MgB₂*’) should have higher values of the RRR (20 \sim 25) with low residual resistivity ($\rho(40\text{ K}) = 0.38 - 1\ \mu\Omega\text{cm}$) and higher MR with a resistivity upturn at low temperature under high magnetic field.^{2,5,6} Insulating impurities and/or local strains were thought to be the causes of any behaviors different from the above.^{10,11,12,16,17} However, recent reports on all single crystals^{18,19,20,21} and many polycrystals^{13,14,15,22} have shown a RRR value of about 5. Moreover, the residual resistivity of single crystals ($\rho_{ab}(40\text{ K}) = 1 - 2\ \mu\Omega\text{cm}$) was higher than that of ‘*highRRR-MgB₂*’.^{18,19,20,21} Thus, it has become an urgent matter to clarify the origin of the different reports on polycrystalline MgB_2 .

Here, we report the transport properties of MgB_2 prepared under different conditions. For samples containing the least amount of unreacted Mg, we found $T_c \simeq 39.2$ K, $\Delta T_c = 0.3 - 0.5$ K, RRR ~ 5.8 , and $\text{MR}_{5T} \sim 3\%$. The last three values are very similar to those reported for single crystals. For the samples containing a relatively large amount of unreacted Mg, the values for ΔT_c , RRR, and MR, were considerably larger. These higher values of RRR and MR are similar to those in *highRRR-MgB₂*. T_c for these samples was about 38 K.

A Ta capsule containing a stoichiometric mixture of Mg chunks and the ^{11}B isotope was heated under 3 GPa in a 12-mm cubic multi-anvil-type press.^{10,23,24,25}

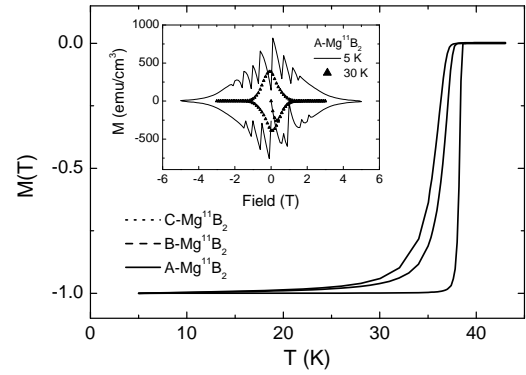


FIG. 1: Normalized magnetization of MgB_2 measured at 20 Oe. The solid line, the dashed, and the dotted lines are for A- MgB_2 , B- MgB_2 , and C- MgB_2 , respectively. T_c was 38 \sim 39 K and ΔT_c was 0.5, 3.5, and 4.5 K, respectively. The inset shows the magnetic hysteresis curve, $M(H)$, of a piece of A- MgB_2 ($m \sim 78$ mg) measured at 5 K and 30 K.

The maximum heating temperature (850 \sim 1000°C) and the preparation of the precursors were varied to obtain different samples. One batch, A- MgB_2 , was heated at 950 \sim 1000°C after enough grinding of the precursors. For B- MgB_2 and C- MgB_2 , the heating temperatures were about 900°C and 850°C respectively, and the precursors were ground less. Details of the high pressure synthesis have been reported previously.^{10,23} The pellet density was 2.48 \sim 2.6 g/cm³ which is quite close to the crystallographic density, a common feature in high-pressure synthesis.^{10,26} As a result, grain connectivity was prevalent over the entire sample (~ 1 mm).

A dc SQUID magnetometer (Quantum Design, MPMSXL), a field-emission scanning electron microscope (SEM), an optical microscope, and an X-ray diffractometer were used for this investigation. The re-

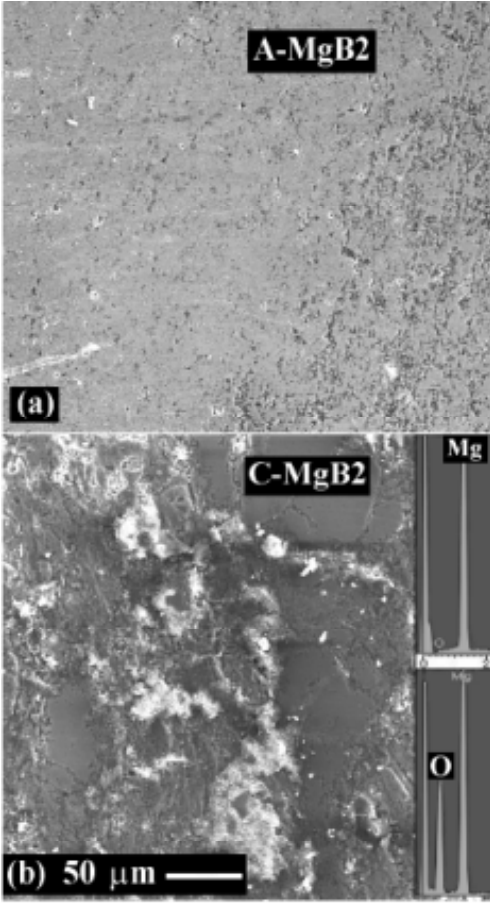


FIG. 2: SEM images of A-MgB₂ and C-MgB₂ at the same magnification with scale bar 50 μm in length: (a) well connected grains in A-MgB₂, (b) Unreacted Mg in C-MgB₂, as large as several tens of μm , are shown as dark islands. For example, see an island under caption of ‘C-MgB₂’.

sistivity, $\rho(T, H)$, was measured by using a standard 4-probe technique on a bar shaped specimen ($\sim 0.5 \times 1 \times 4 \text{ mm}^3$).

Figure 1 shows the normalized magnetization curves $M(T)$ measured at 20 Oe in the zero-field cooled mode for A-MgB₂, B-MgB₂, and C-MgB₂. All samples showed $M/H \gtrsim 150\%$ of $-1/4\pi$, as previously observed.³ The T_c of A-MgB₂ was about 39 K, and its ΔT_c 0.5 K. The values of T_c for B-MgB₂ and C-MgB₂ were slightly lower, but the transition width ΔT_c became much larger, i.e., 3.5 and 4.5 K, respectively.²⁷ The inset in Fig. 1 shows the magnetic hysteresis curves $M(H)$ for A-MgB₂ at 5 K and 30 K; a very clear flux jumping behavior was observed at 5 K. This kind of flux jump has also been reported for commercial MgB₂ (HIP-Alfa) after sintering under 3 GPa.²⁸ Details of this result will be reported elsewhere.²⁹

To search for the origin of the above difference in $M(T)$, we investigated images of cleaved or polished surfaces by using a SEM and an optical microscope. The SEM image for A-MgB₂ in Fig. 2(a) shows well-connected grains, with no clear grain boundaries, over

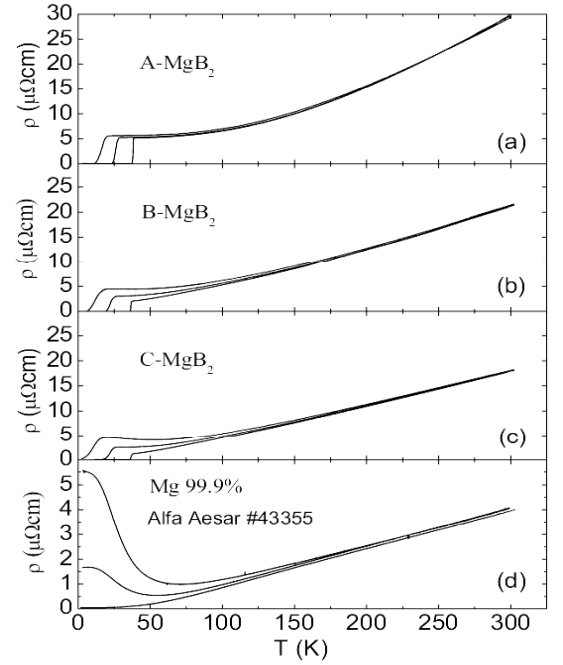


FIG. 3: Resistivity, $\rho(T)$, for various kinds of MgB₂ at 0, 5, and 10 Tesla. (a) The T_c was about 39 K, and the ΔT_c was 0.3 K, the RRR = 5.8 and the values of the MR at 40 K were 3% and 12% at 5 and 10 Tesla for A-MgB₂. (b) For B-MgB₂, RRR = 9.9, and the values of the MR at 40 K were 49% and 111%. (c) For C-MgB₂, RRR = 13.7 and the values of the MR at 40 K were 100% and 224%. (d) Resistivity for Mg (Alfa Aesar #43355). Note that the resistivity upturn below about 50 K became more pronounced at higher fields for C-MgB₂ and the Mg.

a very wide region. However, unreacted Mg was easily identified for C-MgB₂, as shown in Fig. 2(b). The dark islands, as large as several tens of μm , in Fig. 2(b) were identified to be unreacted Mg by a clear Mg peak at 1.25 keV in the energy dispersive spectrum (EDS) in the inset of Fig. 2(b). For example, see an island under caption of ‘C-MgB₂’. Another evidence is that strong Mg peak in XRD pattern such as one near $2\theta \sim 37^\circ$ reported previously¹² was also observed for C-MgB₂. Unreacted Mg grains were also found in B-MgB₂, but were nearly absent in A-MgB₂. The unreacted Mg grains in C-MgB₂ were bigger and had denser population than those in B-MgB₂. The unreacted Mg showed a characteristic white tint when viewed through the optical microscope. All these shows that the basic superconducting parameters T_c and ΔT_c were degraded as the amount of unreacted Mg is increased. For C-MgB₂, insulating MgO impurity was also identified by a clear O peak at 0.52 keV in EDS and was shown as white dots in Fig. 2(b).

To further investigate the effect of unreacted Mg, we measured resistivity under a magnetic field. Figure 3 shows $\rho(T)$ at 0, 5, and 10 T. A-MgB₂ shows the highest T_c , ~ 39 K, and the smallest ΔT_c , ~ 0.3 K. The values of the zero-field resistivity for A-MgB₂ at 40 K and 300 K

were 5.13 and 30.0 $\mu\Omega\text{cm}$, respectively. A RRR value of ~ 5.8 and a MR of 3%(12%) at 5(10) T were also observed. The RRR for all stoichiometric samples prepared under similar conditions had values from ~ 4.5 to ~ 6 . The values of RRR and MR_{5T} were similar to those recently reported for single crystal^{18,30} and polycrystal^{15,22}.

While $\rho(300\text{ K})$ was not much different, the $\rho(40\text{ K})$ of 2.11(1.29) $\mu\Omega\text{cm}$ for B-MgB₂(C-MgB₂) was much smaller than that of A-MgB₂, giving a larger value of RRR = 9.9(13.7). Also, the MR_{5T} increased drastically up to 49% and 100%, as shown in Fig. 3(b) and Fig. 3(c). At a higher field of 10 T, MR_{10T} reached values as large as 111%(224%) for B-MgB₂(C-MgB₂). Another interesting observation is the peculiar resistivity upturn below 50 K for C-MgB₂ at 10 T. A similar upturn had been reported previously for *highRRR-MgB₂*.⁵

Now let's turn our attention to the resistivity behavior of Mg itself. Figure 3(d) shows the resistivity of a pressed bar of a commercial Mg block (Alfa Aesar #43355) measured at 0, 5, and 10 T. The observed temperature dependence of $\rho(T, H = 0)$ with very high RRR value is consistent with that reported in the literature³¹ for pure Mg except for the slightly higher value of 0.12 $\mu\Omega\text{cm}$ at 40 K. The resistivity of Mg under an applied magnetic field shows several interesting features, especially at lower temperatures, such as high MR values and a large resistivity upturn below 50 K. The MR at 5(10) T is more than 400%(1300%) at 40 K, and the resistivity upturn became more pronounced at higher fields. Because $\rho(T)$ of Mg is much smaller than $\rho(T)$ of stoichiometric A-MgB₂ in the region of $T > T_c$ and $H \leq 10$ T, $\rho(T, H)$ of MgB₂ containing unreacted Mg will have some of the character of Mg. The unreacted Mg in MgB₂ will decrease the resistivity at 40 K more than it will at 300 K, as observed in Figs. 3(b) and 3(c), so the result-

ing increase in the RRR should be accompanied by an increase in the MR. Moreover, the Mg in C-MgB₂ also explains the resistivity upturn below 50 K at 10 T.

Incomplete reaction of polycrystalline MgB₂ due to either unoptimized growth conditions or a Mg-rich precursor may result in unreacted Mg.³² Unlike the insulting oxide impurities in high- T_c cuprates, unreacted conducting Mg may not be so detrimental in bulk transport applications of MgB₂, especially for the case of quenching of the superconductivity. However, if a correct understanding of the intrinsic properties of MgB₂ such as resistivity, which can be screened by the unreacted conducting Mg impurities, is to be obtained, then phase-pure MgB₂ is essential.

In conclusion, we synthesized MgB₂ and investigated systematically the effect of unreacted Mg in the MgB₂ on its transport properties. For the stoichiometric MgB₂, RRR was ~ 5.8 , and MR_{5T} was $\sim 3\%$. We found that the larger transition width and the higher values of the RRR and the MR were due to the unreacted Mg in the MgB₂. The appearance of peculiar resistivity upturn at a lower temperatures at higher field of 10 T was also explained as being due to the unreacted Mg in the MgB₂ materials. This conclusion is also supported by the results for single crystals of MgB₂.

Acknowledgments

This work is supported by the Ministry of Science and Technology of Korea through the Creative Research Initiative Program. We appreciate valuable discussions with S.-W. Cheong and Y. S. Song.

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